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(71) Applicant: **SILTRONIC AG** [DE/DE]; Einsteinstr. 172
Tower B / Blue Tower, 81677 München (DE).

(72) Inventors: **BECKER, Lucas**; Sportplatzstr. 9 B, 94436
Simbach (DE). **STORCK, Peter**; Descartesstraße 20,
84489 Burghausen (DE).

(74) Agent: **SILTRONIC AG** et al.; STAUDACHER, Wolf-
gang, Johannes-Hess-Str. 24, 84489 Burghausen (DE).

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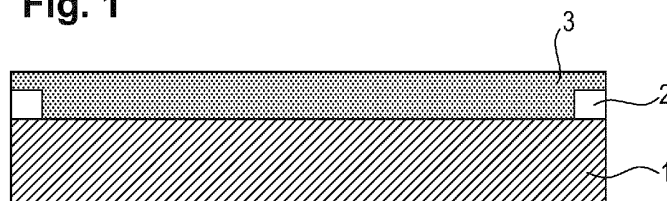
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(54) Title: METHOD FOR DEPOSITING A SILICON GERMANIUM LAYER ON A SUBSTRATE

Fig. 1



(57) Abstract: A method for heteroepitaxially depositing a silicon germanium layer (3) on a substrate (1), comprising: providing a mask layer (4) atop the substrate (1); removing an outer section of the mask layer (4) to provide access to an annular-shaped free surface (6) of the substrate in an edge region of the substrate surrounding a remainder (5) of the mask layer (4); depositing a cylindrical silicon germanium layer (2) atop the annular-shaped free surface (6) of the substrate; removing the remainder of the mask layer; and depositing the silicon germanium layer (3) atop the substrate (1) and atop the cylindrical silicon germanium layer (2), the silicon germanium layer (3) contacting an inner lateral surface of the cylindrical silicon germanium layer (2).



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